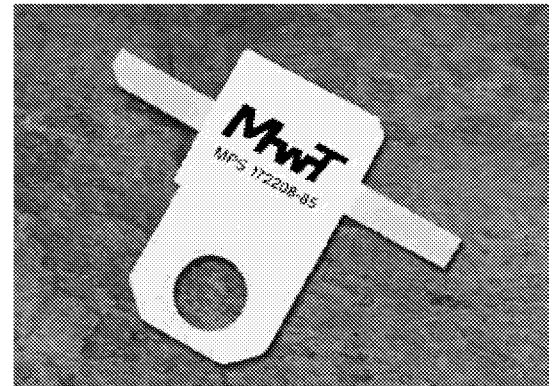


Features

- +38 dBm Typical IP3
- +26.0 dBm Typical P1dB
- 13.0 dB Typical Gain
- +7.5 Volt Bias
- 25% Power Added Efficiency



Description

The MPS-172208-85 is a narrowband, self-biased GaAs FET amplifier designed for digital communications applications where excellent linearity is required. Typical applications include driver stages for DCS-1800, PCS-1900, PHS and DECT systems. The amplifier is directly connected to a 50 Ω microstrip circuit without additional matching elements.

Electrical Specifications at 25°C, V_{dd} = 7.5 V, Z_o = 50 Ω

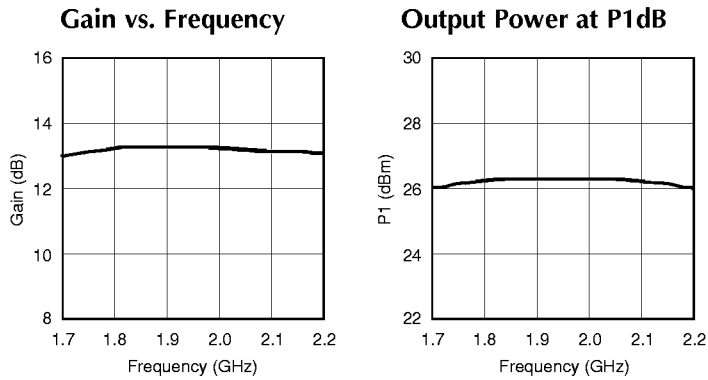
Symbol	Parameter	Minimum	Typical	Maximum	Unit
Freq	Frequency Range	1900		2000	MHz
SSG	Small Signal Gain	12	13		dB
P1dB	Pout at 1 dB Compression	+25.0	+26.0		dBm
IP3	Third-order Intercept ¹		+38.0		dBm
NF	Noise Figure		5.0		dB
VSWR	Input/Output VSWR		2.0:1	2.5:1	
Δ GOF	Gain Variation over Frequency		± 0.2	± 0.5	dB
Δ GOT	Gain Variation over Temperature			-0.16	dB/°C
I _{dd}	DC Current		170	300	mA
PAE	Power Added Efficiency		25		%

¹ Two tone tests at Pout = +10 dBm for each tone; centered at 1950 MHz with 20 MHz separation.

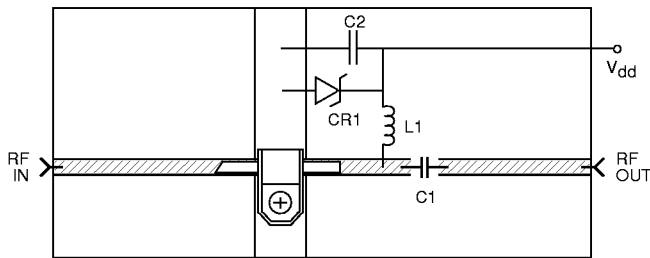
Absolute Maximum Ratings

Maximum Bias Voltage	8.0 V
Maximum Continuous RF Input Power	480 mW
Maximum Peak Input Power	720 mW
Maximum Case Operating Temperature	+85°C
Maximum Storage Temperature	-65°C to +150°C

Typical Performance at 25°C



Application Circuit

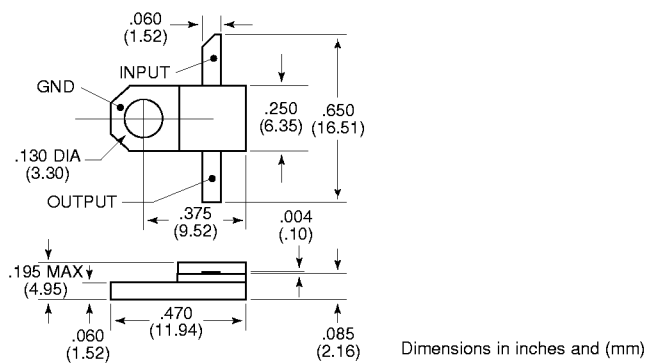


C1	100 pF	Chip Capacitor
C2	.22 μ F	Capacitor
L1	160 nH	Printed or Wound Coil
CR1	8.0 V	Zener Diode
		50 Ω Microstrip Line

Board material FR-4 or equivalent.

Outline Diagram

Half Flange Package (-85)



Ordering Information

Part Number	Package
MPS-172208-85	Half Flange Package
MPS-172208-85EV	Half Flange Package on Evaluation Board